## **Transistor PNP, TO-18**



### **Pin Configuration** 1. Emitter 2 3 3. Collector

2. Base

#### **Absolute Maximum Ratings**

Description	Symbol	Value	Units
Collector Emitter Voltage	Vceo	40	
Collector Base Voltage	Vсво	Vсво 60 V   VЕВО 5 V	
Emitter Base Voltage	Vebo		
Collector Current Continuous	lc	600	mA
Power Dissipation at T <sub>A</sub> = 25°C Derate above 25°C	D-	400 2.28	mW mW/°C
Power Dissipation at Tc = 25°C Derate above 25°C	Po	1.8 10.3	W mW/ °C
Operating and Storage Junction Temperature Range	Tj, Tstg	-65 to +200	°C

### Electrical Characteristics: (Tc = +25°C unless specified otherwise)

Description	Symbol	Test Condition	Min.	Max.	Units
Collector Emitter Voltage	*Vceo	Ic = 10mA, Iв = 0	40	-	
Collector Base Voltage	Vсво	Ic = 10μΑ, Iε = 0	60	-	V
Emitter Base Voltage	Vebo	Iε = 10μΑ, Ic = 0	5	-	
Collector Cut off Current	ICEX	Vce = 30V, Vbe = 0.5V	-	50	
		Vcb = 50V, IE = 0	-	20	nA
Collector Cut off Current	Ісво	V <sub>CB</sub> = 50V, IE = 0, Та = 150°С	-	20	А
Base Current	Ів	Vce = 30V, VBE = 0.5V	-	50	nA
DC Current Gain	hfe	Ic = 0.1mA, VcE = 10V Ic = 1mA, VcE = 10V Ic = 10mA, VcE = 10V *Ic = 150mA, VcE = 10V *Ic = 500mA, VcE = 10V	-	>35 >50 >75 100 - 300 >30	-

\*Pulse Test: Pulse Width ≤300µs, Duty Cycle ≤2%

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Description	Symbol	Test Condition	Min.	Max.	Units	
Small Signal Characteristics	· · ·				•	
Collector Emitter Saturation Voltage	*Vce(sat)	Ic = 150mA, Iв = 15mA Ic = 500mA, Iв = 50mA	-	0.4 1.6		
Base Emitter Saturation Voltage	*Vbe(sat)	Ic = 150mA, Iв = 15mA Ic = 500mA, Iв = 50mA	-	1.3 2.6		
Transition Frequency	** <b>f</b> ⊤	Ic = 50mA, Vce = 20V f = 100MHz	200	-	MHz	
Output Capacitance	Сово	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0 f = 100КНz	-	8	-5	
Input Capacitance	Сіво	$V_{BE} = 2V, I_{C} = 0$ $f = 100KHz$	-	30	pF	
Description	Symbol	Test Condition	Min.	Max.	Units	
Switching Time						
Delay Time	ta		-	10		
Rise Time	tr	Ic = 150mA, Iв1 = 15mA, Vcc = 30V	-	40	1	
Turn on Time	ton	VCC - 30V	-	45	]	
Storage Time	ts		-	80	- nS	

Ic = 150mA, IB1 = IB2 = 15mA,

Vcc = 6V

\*Pulse Test: Pulse Width ≤300µs, Duty Cycle ≤2%

\*\*fT is defined as the frequency at which /hFE/ extrapolates to unity

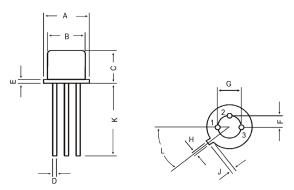
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toff

#### **TO-18 Metal Can Package**

Fall Time

Turn off Time



Dim.	Min.	Max.
А	5.24	5.84
В	4.52	4.97
С	4.31	5.33
D	0.4	0.53
E	-	0.76
F	-	1.27

Dim.	Min.	Max.
G	-	2.97
Н	0.91	1.17
J	0.71	1.21
К	12.7	-
L	45°	-

30

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**Dimensions : Millimetres** 

#### Part Number Table

Description	Part Number		
Transistor, PNP, TO-18	2N2907		

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